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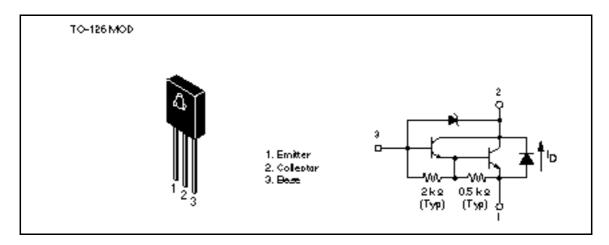
Silicon NPN Epitaxial

HITACHI

Application

Low frequency power amplifier

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I _c	1.5	A
Collector peak current	C (peak)	3.0	A
Collector power dissipation	P _c	10	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
C to E diode forward current	I _D *1	1.5	A

Note: 1. Value at $T_c = 25$ °C.

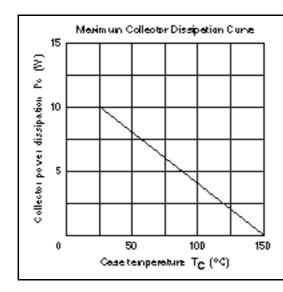


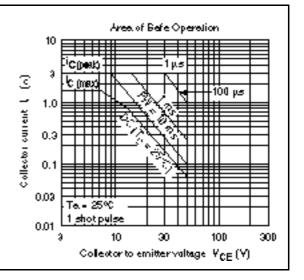
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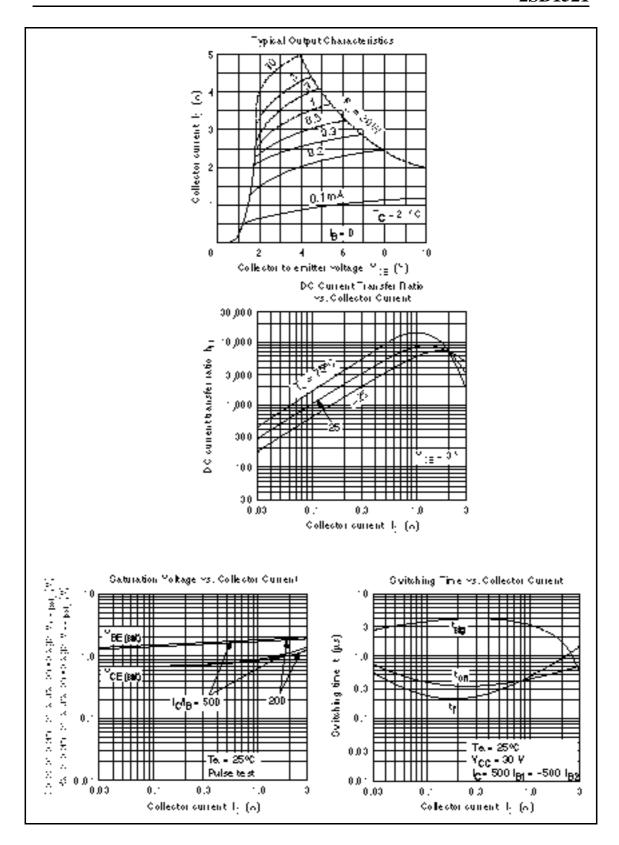
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage (Zener breakdown voltage)	V _{(BR)CBO} [V _z]	50	60	70	V	$I_{c} = 0.1 \text{ mA}, I_{E} = 0$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	_	_	V	$I_{E} = 50 \text{ mA}, I_{C} = 0$
Collector cutoff current	I _{CEO}	_	_	10	μA	V _{CE} = 50 V, R _{BE} =
DC current transfer ratio	h _{FE}	2000	_	30000		$V_{CE} = 3 \text{ V}, I_{C} = 1 \text{ A}^{*1}$
Collector to emitter saturation	V _{CE (sat)1}	_	_	1.5	V	$I_{\rm C} = 1 \text{ A}, I_{\rm B} = 1 \text{ mA}^{*1}$
voltage	V _{CE (sat)2}	_	_	2.0	V	$I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 1.5 \text{ mA}^{*1}$
Base to emitter saturation	V _{BE (sat)1}	_	_	2.0	V	$I_{\rm C} = 1 \text{ A}, I_{\rm B} = 1 \text{ mA}^{*1}$
voltage	V _{BE (sat)2}	_	_	2.5	V	$I_{\rm C} = 1.5 \text{ A}, I_{\rm B} = 1.5 \text{ mA}^{*1}$
C to E diode forward voltage	V _D	_	_	3.0	V	I _D = 1.5 A
Turn on time	Ton	_	0.5	_	μs	$I_{C} = 1 \text{ A}, I_{B1} = -I_{B2} = 1 \text{ mA}$
Turn off time	Toff	_	2.0	_	μs	_

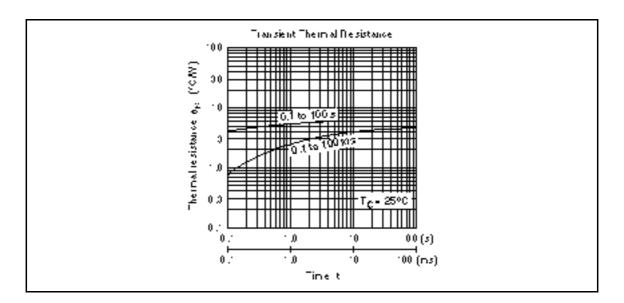
Note: 1. Pulse test.







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